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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant(s): Chen *et al.*

Examiner: Whitmore, Stacy

Serial No.: 10/711,418

Art Unit: 2825

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Title: **NON-DESTRUCTIVE EVALUATION OF MICROSTRUCTURE AND  
INTERFACE ROUGHNESS OF ELECTRICALLY CONDUCTIVE LINES IN  
SEMICONDUCTOR INTEGRATED CIRCUITS IN DEEP SUB-MICRON  
REGIME**

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Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**OFFICE ACTION RESPONSE**

Sir:

This communication is in response to the Office Action mailed October 23, 2006.

On Friday, December 15, 2006, Applicants' representative Khoi D. Nguyen and Examiner Stacy Whitmore talked over the phone and came to the following agreements:

- (A) there are 20 claims,
- (B) a flow chart showing the steps of claim 1 is required,
- (C) a new title of the invention suggested by representative Khoi D. Nguyen is acceptable,

and

- (D) an additional step (e) to claim 1 suggested by representative Khoi D. Nguyen is acceptable.